

# 单 P 沟道 MOSFET

ELM55039SA-S

<http://www.elm-tech.com>

## ■概要

ELM55039SA-S 是 P 沟道低输入电容，低工作电压，低导通电阻的大电流 MOSFET。

## ■特点

- $V_{ds} = -100V$
- $I_d = -25A$
- $R_{ds(on)} = 90m\Omega$  ( $V_{gs} = -10V$ )
- $R_{ds(on)} = 100m\Omega$  ( $V_{gs} = -4.5V$ )

## ■绝对最大额定值

如没有特别注明时,  $T_a = 25^\circ C$

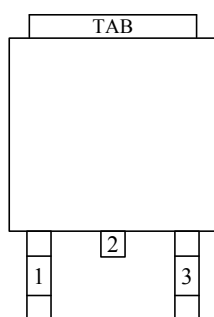
项目	记号	规格范围	单位	
漏极 - 源极电压	$V_{ds}$	-100	V	
栅极 - 源极电压	$V_{gs}$	$\pm 20$	V	
漏极电流 (定常) $T_j = 150^\circ C$	Id	$T_a = 25^\circ C$	-25.0	A
		$T_a = 70^\circ C$	-15.0	
漏极电流 (脉冲)	$I_{dm}$	-50	A	
容许功耗	Pd	$T_c = 25^\circ C$	40	W
		$T_c = 70^\circ C$	15	
动作结合部温度	$T_j$	150	$^\circ C$	
保存温度范围	$T_{stg}$	-55 ~ 150	$^\circ C$	

## ■热特性

项目	记号	典型值	最大值	单位
最大结合部 - 环境热阻	$R_{\theta ja}$		62.5	$^\circ C/W$

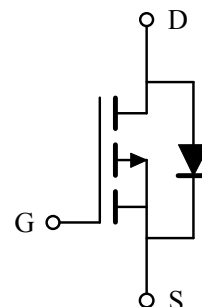
## ■引脚配置图

TO-252-3(俯视图)



引脚编号	引脚名称
1	GATE
2	DRAIN
3	SOURCE

## ■电路图



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## ■电特性

如没有特别注明时,  $T_a=25^\circ\text{C}$

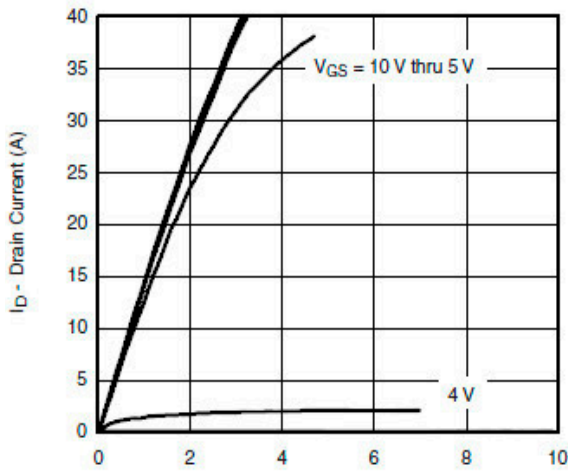
项目	记号	条件	最小值	典型值	最大值	单位
<b>静态特性</b>						
漏极 - 源极击穿电压	BV <sub>dss</sub>	$I_d=-250\mu\text{A}, V_{gs}=0\text{V}$	-100			V
栅极接地时漏极电流	I <sub>dss</sub>	$V_{ds}=-80\text{V}$ $V_{gs}=0\text{V}$			-1	$\mu\text{A}$
		$T_a=85^\circ\text{C}$			-30	
栅极漏电流	I <sub>gss</sub>	$V_{ds}=0\text{V}, V_{gs}=\pm 20\text{V}$			$\pm 100$	nA
栅极阈值电压	V <sub>gs(th)</sub>	$V_{ds}=V_{gs}, I_d=-250\mu\text{A}$	-1.0		-2.5	V
导通时漏极电流	I <sub>d(on)</sub>	$V_{gs}=-10\text{V}, V_{ds}\geq -10\text{V}$	-25			A
漏极 - 源极导通电阻	R <sub>ds(on)</sub>	$V_{gs}=-10\text{V}, I_d=-12\text{A}$		80	90	m $\Omega$
		$V_{gs}=-4.5\text{V}, I_d=-8\text{A}$		88	100	
正向跨导	G <sub>fs</sub>	$V_{ds}=-15\text{V}, I_d=-5.2\text{A}$		19		S
二极管正向压降	V <sub>sd</sub>	$I_s=-2.0\text{A}, V_{gs}=0\text{V}$		-0.8	-1.3	V
寄生二极管最大连续电流	I <sub>s</sub>				-8.0	A
<b>动态特性</b>						
输入电容	C <sub>iss</sub>	$V_{gs}=0\text{V}, V_{ds}=-60\text{V}, f=1\text{MHz}$		4300		pF
输出电容	C <sub>oss</sub>			280		pF
反馈电容	C <sub>rss</sub>			220		pF
<b>开关特性</b>						
总栅极电荷	Q <sub>g</sub>	$V_{gs}=-10\text{V}, V_{ds}=-75\text{V}$ $I_d\equiv -5.2\text{A}$		85	150	nC
栅极 - 源极电荷	Q <sub>gs</sub>			18		nC
栅极 - 漏极电荷	Q <sub>gd</sub>			28		nC
导通延迟时间	t <sub>d(on)</sub>	$V_{gs}=-10\text{V}, V_{ds}=-75\text{V}$ $R_L=16\Omega, I_d\equiv -4.8\text{A}$ $R_{gen}=6.0\Omega$		25	50	ns
导通上升时间	t <sub>r</sub>			45	85	ns
关闭延迟时间	t <sub>d(off)</sub>			115	200	ns
关闭下降时间	t <sub>f</sub>			65	130	ns

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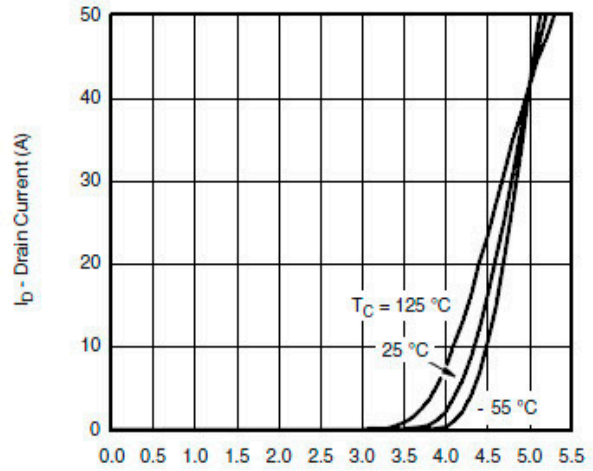
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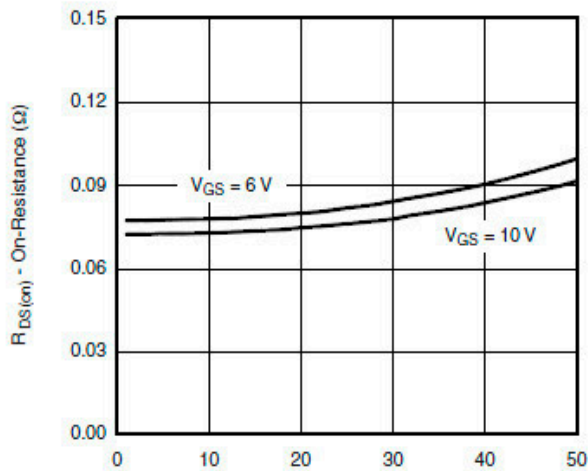
## ■ 标准特性和热特性曲线



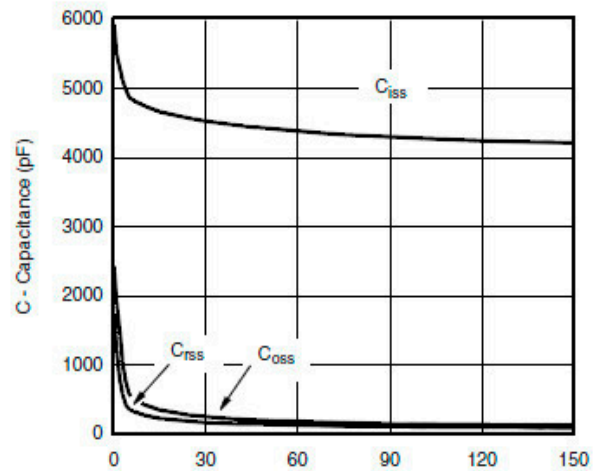
$V_{DS}$  - Drain-to-Source Voltage (V)  
**Output Characteristics**



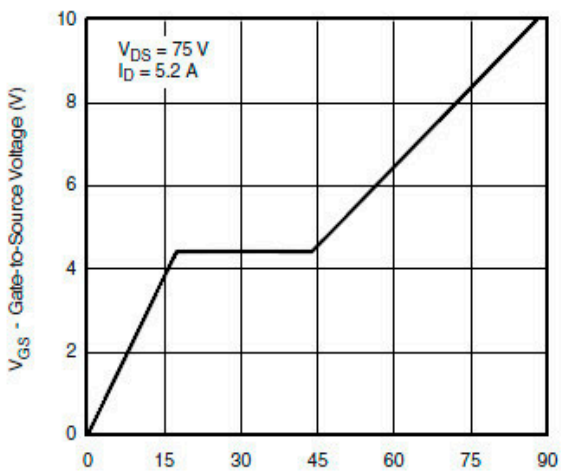
$V_{GS}$  - Gate-to-Source Voltage (V)  
**Transfer Characteristics**



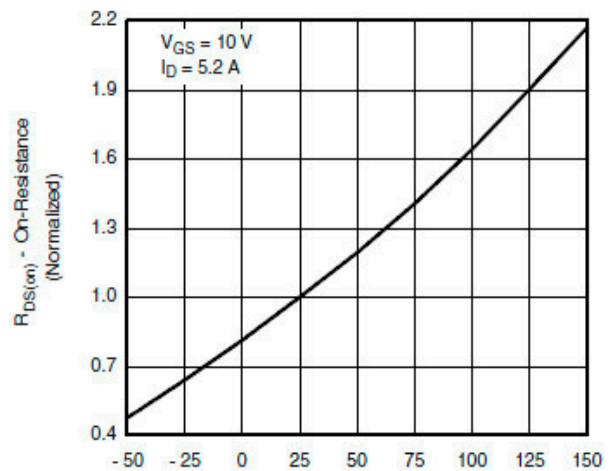
$I_D$  - Drain Current (A)  
**On-Resistance vs. Drain Current**



$V_{DS}$  - Drain-to-Source Voltage (V)  
**Capacitance**



$Q_g$  - Total Gate Charge (nC)  
**Gate Charge**

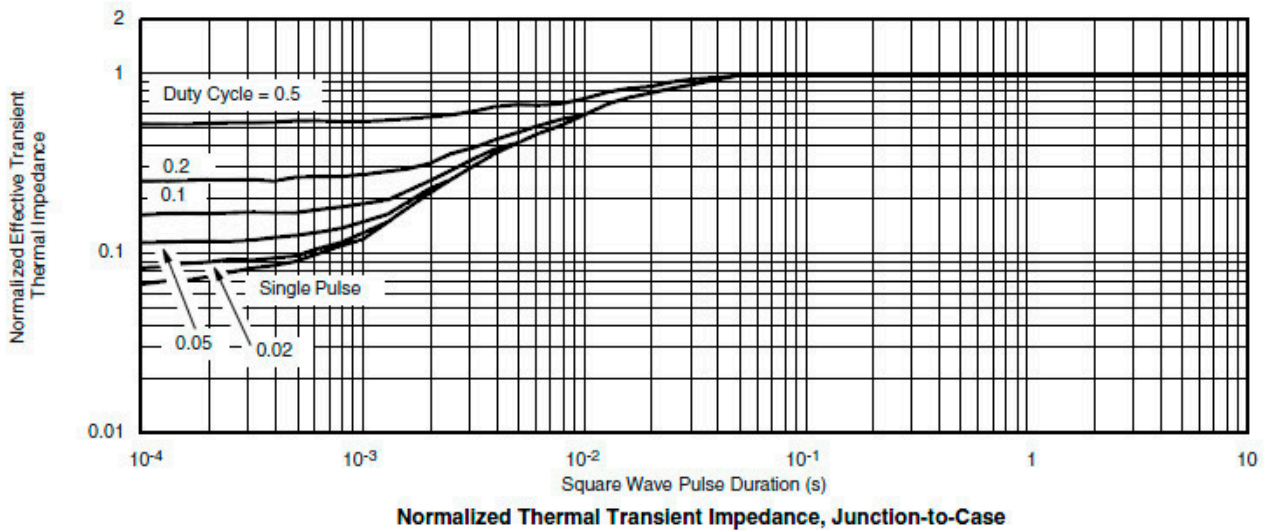
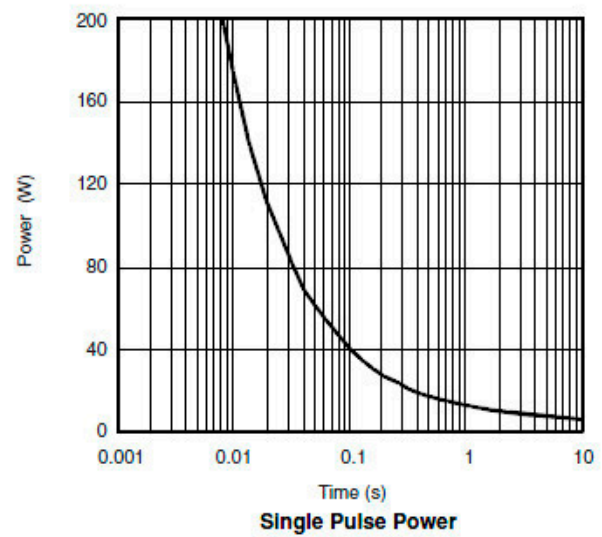
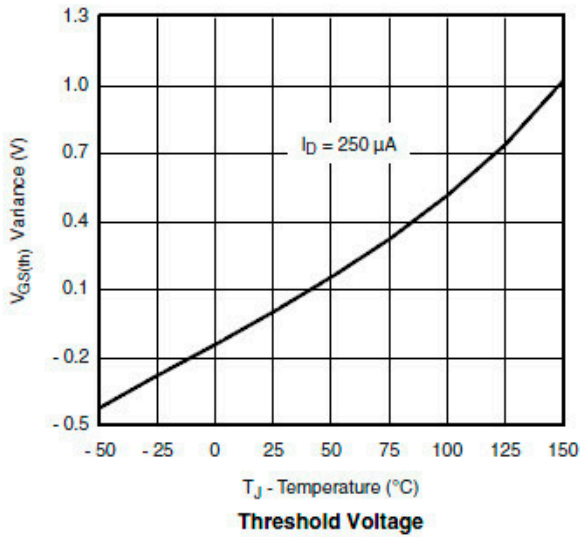
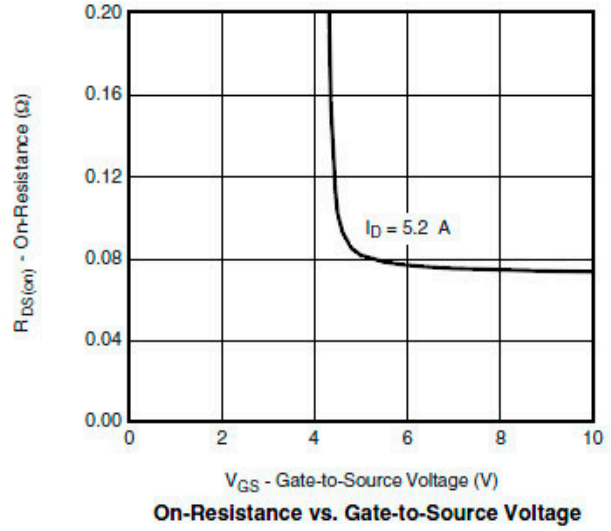
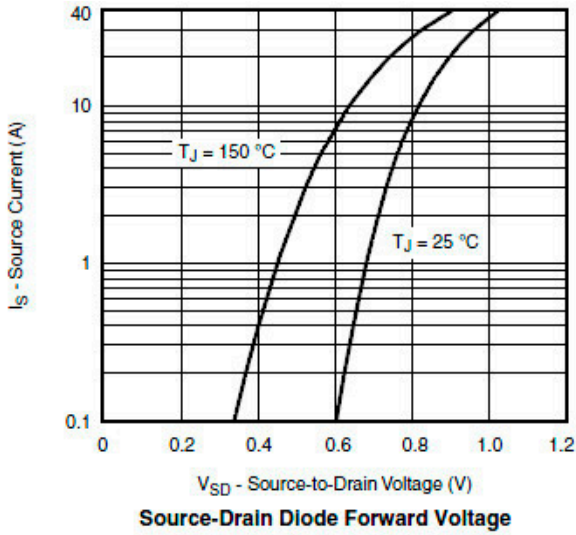


$T_J$  - Junction Temperature ( $^\circ\text{C}$ )  
**On-Resistance vs. Junction Temperature**

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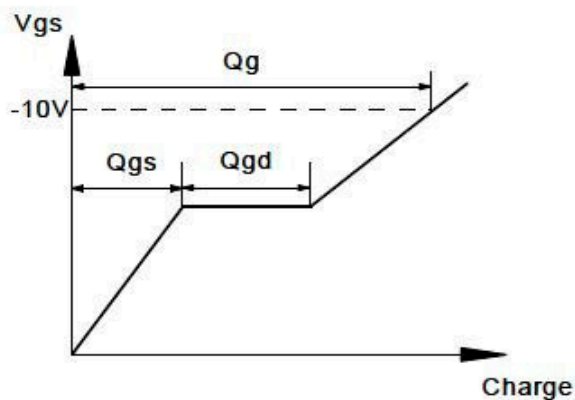
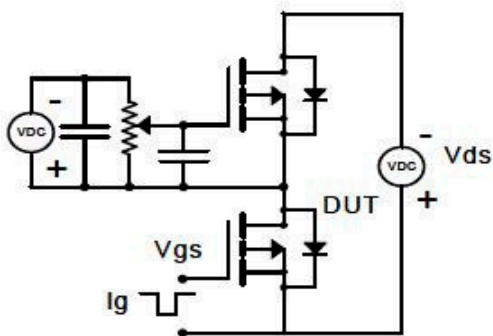
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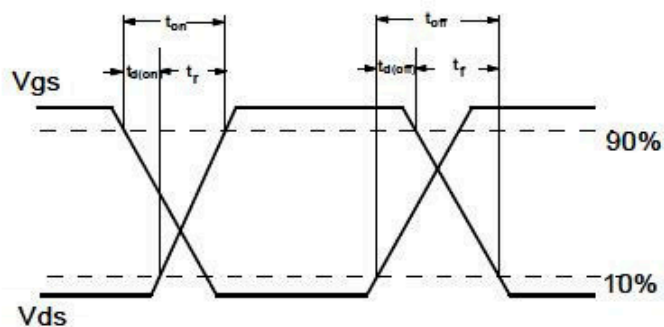
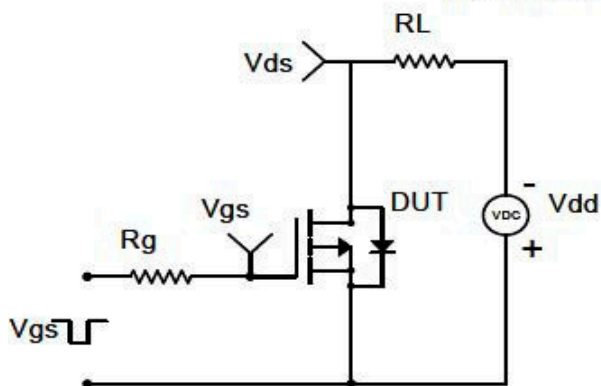
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## 测试电路和波形

### Gate Charge Test Circuit & Waveform



### Resistive Switching Test Circuit & Waveforms



### Diode Recovery Test Circuit & Waveforms

